

## N-Channel 40-V (D-S) MOSFET

### Description

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low RDS(on) and to ensure minimal power loss and heat dissipation.

Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, and PCMCIA cards, cellular and cordless telephones.

#### Features

• Low rDS(on) provides higher efficiency and extends battery life

• Miniature SO-8 surface mount package saves board space

- High power and current handling capability
- Low side high current DC-DC Converter applications
- RoHS compliant package

### Package type : SO-8

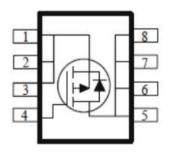
**Packing & Order Information** 

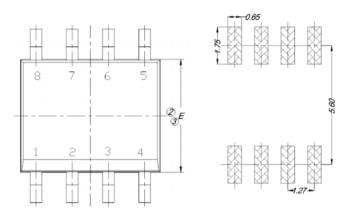
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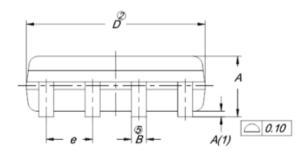


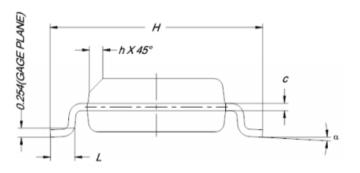


Graphic symbol









DIM	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	
Α	1.35	1.55	1.75	
A(1)	0.10	0.18	0.25	
В	0.38	0.45	0.51	
С	0.19	0.22	0.25	
D	4.80	4.90	5.00	
E	3.80	3.90	4.00	
е	1.27 BSC			
н	5.80	6.00	6.20	
L	0.50	0.72	0.93	
α	0°	4°	8°	
h	0.25	0.38	0.50	



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### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (T <sub>A</sub> =25°C unless otherwise specified)					
Symbol	Parameter	Value	Unit		
V <sub>DS</sub>	Drain-Source Voltage	40	V		
V <sub>GS</sub>	Gate-Source Voltage	±20	V		
т	Continuous Drain Current <sup>a</sup> (T <sub>A</sub> =25°C)	±9.7	А		
$I_D$	Continuous Drain Current <sup>a</sup> (T <sub>A</sub> =70°C)	±7.2	А		
I <sub>DM</sub>	Pulsed Drain Current <sup>b</sup>	±50	А		
Is	Continuous Source Current (Diode Conduction) <sup>a</sup>	2.3	А		
P <sub>D</sub>	Power Dissipation <sup>a</sup> ( $T_A = 25^{\circ}C$ )	3.1	W		
	Power Dissipation <sup>a</sup> ( $T_A = 70^{\circ}C$ )	2.2	W		
$T_J/T_{STG}$	Operating Junction and Storage Temperature	-55 to +150	°C		

Thermal Resistance Ratings						
Symbol	Parameter	Maximum	Units			
R <sub>θJA</sub>	Maximum Junction-to-Ambient <sup>a</sup> (t <= 10 sec)	50	°C/W			
	Maximum Junction-to-Ambient <sup>a</sup> (Steady-State)	92	C/ W			

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

Static						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
$V_{GS(th)}$	Gate-Threshold Voltage	$V_{\rm DS}=V_{\rm GS}$ , $I_{\rm D}=$ -250 $\mu A$	1			v
Igss	Gate-Body Leakage	$V_{DS}=0\ V$ , $V_{GS}=20\ V$			±100	nA
Idss	Zero Gate Voltage Drain Current	$\begin{split} V_{DS} &= 24 \ V \ , \ V_{GS} = 0 \ V \\ V_{DS} &= 24 \ V \ , \ V_{GS} = 0 \ V \ , \ T_J = 55^\circ C \end{split}$			1 25	uA
I <sub>D(on)</sub>	On-State Drain Current	$V_{\rm DS}=5~V$ , $V_{\rm GS}=10~V$	20			A
<sup>r</sup> DS (on)	Drain-Source On-Resistance				22 27	mΩ
g fs	Forward Tranconductance	$V_{DS} = 15 V$ , $I_D = 9.7 A$		40		S
Vsd	Diode Forward Voltage	$I_S = 2.3 \text{ A}$ , $V_{GS} = 0 \text{ V}$		0.7		V

Dynamic <sup>b</sup>							
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units	
Qg	Total Gate Charge	$V_{DS} = 15 \ V \ , \ I_D = 9.7 \ A \ , \ V_{GS} = 4.5 \ V \ . \label{eq:VDS}$		12.5		nC	
Qgs	Gate-Source Charge			2.6		nC	
$\mathbf{Q}_{\mathrm{gd}}$	Gate-Drain Charge			4.6		nC	



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Dynamic <sup>b</sup>							
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units	
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 25 \ V \ , \ R_L = 25 \ \Omega \ , \ V_{GEN} = 10 \ V \ , \ I_D = 1 \ A$		20		ns	
tr	Rise Time			9		ns	
t <sub>d(off)</sub>	Turn-Off Delay Time			70		ns	
tf	Fall Time			20		ns	

Notes:

a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.



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